PATENT COOPERATION TREATY

PCT

TRANSLATION INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

(Chapter II of the Patent Cooperation Treaty)

(PCT Article 36 and Rule 70)

Applicant's or agent's file reference PF16808			FOR FURTHER ACTION		See Form PCT/IPEA/416		
International application No.		Ir	International filing date (day/month/year)		Priority date (day/month/year)		
PCT/JP2004/013158		158	09.09.2004		09.09.2003		
		• •	al classification and				
Applicant ASAHI K	ASEI KAI	BUSHIKI	KAISHA				
	 This report is the international preliminary examination report, established by this International Preliminary Examining Authority under Article 35 and transmitted to the applicant according to Article 36. 						
2. This R	2. This REPORT consists of a total of sheets, including this cover sheet.						
3. This re	port is also accor	mpanied by ANN	EXES, comprising	:			
a. 🔀	a. (sent to the applicant and to the International Bureau) a total of 10 sheets, as follows:						
	sheets				n amended and are the basis for this report and/or Rule 70.16 and Section 607 of the Administrative		
	sheets which supersede earlier sheets, but which this Authority considers contain an amendment that goes beyond the disclosure in the international application as filed, as indicated in item 4 of Box No. I and the Supplemental						
, _	Box.	Intermedianal Pro	many ambul a total of	(indicate type and numb	ber of electronic carrier(s))		
b	(sent to the l	іпіетанопаі Би	reau only) a lotal of	(indicate type and num	per of electronic carrier(s))		
	, containing a sequence listing and/or tables related thereto, in computer readable form only, as indicated in the Supplemental Box Relating to Sequence Listing (see Section 802 of the Administrative Instructions).						
4. This re	port contains ind	ications relating	to the following ite	ms:	W-4 		
	Box No. I	Basis of the re	port				
	Box No. II	Priority					
	Box No. III	·	nent of opinion witl	h regard to novelty, inve	ntive step and industrial applicability		
$\overline{\boxtimes}$	Box No. IV	Lack of unity of	-				
\boxtimes	Box No. V	Reasoned state			velty, inventive step or industrial applicability;		
	Box No. VI	Certain docum	ents cited				
	Box No. VII	Certain defects	in the international	l application			
	Box No. VIII	Certain observ	ations on the intern	ational application			
Date of submissi	on of the demand	1		Date of completion of	this report		
					-		
Name and mailing address of the IPEA/JP				Authorized officer			
Facsimile No.				Telephone No.			

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Box	No. I	Basis of the report				
1.		h regard to the language, this report is based on the internationated under this item.	onal application in the language in	which it was filed, unless otherwise		
	This report is based on translations from the original language into the following language which is the language of a translation furnished for the purposes of:					
		international search (Rule 12.3 and 23.1(b))				
		publication of the international application (Rule 12.4	1)			
		international preliminary examination (Rule 55.2 and	•			
2.	With regard to the elements of the international application, this report is based on (replacement sheets which have been furnished to the receiving Office in response to an invitation under Article 14 are referred to in this report as "originally filed" and are not annexed to this report): the international application as originally filed/furnished					
	\bowtie	the description:				
		pages 1-2,4,7-10,12,14-40		as originally filed/furnished		
		pages* 3,5,6,6/1,11,13	received by this Authority on	04.06.2005		
		pages*	received by this Authority on	· · · · · · · · · · · · · · · · · · ·		
	\boxtimes	the claims:				
		nos. 2-12,14-22,24-28		as originally filed/furnished		
		nos.*	as amended (togethe	r with any statement) under Article 19		
			received by this Authority on	•		
			_ received by this Addiorny on	·		
		the drawings:				
		sheets 1-15		as originally filed/furnished		
		sheets*				
		sheets*	received by this Authority on			
	Ш	a sequence listing and/or any related table(s) - see Suppler	nental Box Relating to Sequence L	isting.		
3.		The amendments have resulted in the cancellation of:				
		the description, pages				
		the claims, nos.				
		the drawings, sheets/figs				
		the sequence listing (specify):				
		any table(s) related to sequence listing (specify):				
4.		This report has been established as if (some of) the amen they have been considered to go beyond the disclosure as f				
		the description, pages				
		the claims, nos.				
		the drawings, sheets/figs				
		the sequence listing (specify):				
*	If ite	em 4 applies, some or all of those sheets may be marked "suj				

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Box	Box No. IV Lack of unity of invention	
1.	.,	-
	restricted the claims.	
	paid additional fees.	
	paid additional fees under protest.	
	neither restricted the claims nor paid additional fees.	
2.	2. This Authority found that the requirement of unity of invention is not complied with and chose the applicant to restrict or pay additional fees.	, according to Rule 68.1, not to invite
3.	3. This Authority considers that the requirement of unity of invention in accordance with Rules 13.1, 13	.2 and 13.3 is:
	complied with.	
	not complied with for the following reasons:	
	Claim 1 can be considered to set for	th an
	invention that is characterized by the feat	cure wherein
	an infrared sensor configured from an InSb	based
	compound semiconductor is packaged in a hyb	orid
	configuration, whereas claims 13 and 23 car	ı be
	considered to set forth inventions that are)
	characterized by the layered structure of t	the infrared
	sensor that is configured from an InSb base	ed compound
	semiconductor.	
	Such being the case, claims 1 to 12 a	and claims
	13 to 28 do not share a common feature that	can be
	considered to be a special technical featur	ce in the
	meaning of PCT Rule 13.2.	
		-1:+i
4.		meauon:
	all parts.	
	the parts relating to claims Nos.	

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Box No. V Reasoned statement under Ar citations and explanations sup			rticle 35(2) with regard to novelty, inventive step or industrial applicability; apporting such statement	
1. Statemen	nı		·	
Nove	elty (N)	Claims	1-28	YES
		Claims		NO
Inve	Inventive step (IS)		13-28	YES
		Claims	1-12	NO
Industrial applicability (IA)		Claims	1-28	YES
		Claims		NO
0 67 67				

- 2. Citations and explanations (Rule 70.7)
 - Document 1: WO 96/05621 A (SRI INTERNATIONAL)
 - Document 2: K. YAMAMOTO et al., "Development of a JFET amplified InSb infrared detector array for use at liquid helium temperature," SPIE, Vol. 1157, Infrared Technology XV (1989), pages 338 to 349
 - Document 3: E. MICHEL et al., "Sb-based infrared materials and photodetectors for the 3-5 and 8-12 μm range," The International Society for Optical Engineering, Proceedings of SPIE Vol. 2685, Photodetectors: Materials and Devices, April 1996, pages 101 to 111
 - Document 4: JP 62-257773 A (Toshiba Corp.)
 - Document 5: JP 6-196745 A (NEC Corp.)
 - Document 6: US 5455421 A (Spears)
 - Document 7: Shinpan Denki Kogaku Handbook, Shadan Hojin Denki Gakkai, pub. Showa 63 Nen (1988), Kiso Bumon Vol. 8: Denshi Device, Chapter 9: Hybrid IC, pages 376 to 378
 - (1) Document 1 indicates that in the past, InSb based materials and the like were used to configure infrared ray detection devices. Therein, document 1 also discloses

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Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement

various features, including the feature wherein infrared ray detection devices are produced by means of a monolithic integration technique whereby an InSn based compound or the like is provided upon a GaAs substrate and then an integrated circuit is mounted upon the same chip (pages 1 to 2).

Consequently, the invention that is set forth in claim 1, wherein the compound infrared ray sensor unit and the integrated circuit unit are arranged in a hybrid layout, is different from the invention that is disclosed in document 1, wherein the compound infrared ray sensor unit and the integrated circuit unit are mounted in a monolithic manner.

However, given the content of the disclosures in document 7 (...make a comparison of hybrid integrated circuits, which are also referred to as mixed integrated circuits, and monolithic integrated circuits (semiconductor integrated circuits) wherein the circuit has been formed within the silicon chip. ... Hybrid integrated circuits and monolithic integrated circuits have slightly different characteristics, and are generally serve complementary roles. For example, hybrid integrated circuits are often used in the initial stages of the development of a new products such a electronic devices, and are also commonly used in power source circuits, output circuits, electric motor drive circuits, sensor circuits and the like."), both monolithic configurations and hybrid configurations can be considered to have been well known as techniques for integrating an infrared ray sensor unit and an integrated circuit unit at the time the present application was filed. Such being the case, it would have been obvious to

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a person skilled in the art that it is possible to select either configuration according to the degree of integration of the elements, the size of the package and the like.

As a result, claim 1 cannot be considered to involve an inventive step in the light of document 1.

(2) The inventions set forth in claims 2 to 12 differ from the invention that is disclosed in document 1 in that document 1 does not make any specific disclosures with regards to the structure of the InSb infrared ray sensor.

However, documents 3 to 6 all disclose InSn infrared ray sensors, and document 3 discloses the feature of employing a p-i-n structure or a heterostructure and the feature of using Sn or Zn as the n-type dopant or the p-type dopant; document 4 discloses the feature of providing a buffer layer of InAsSb or the like and the feature of employing a pn structure; document 5 discloses the feature of employing an AlGaSb/InAs superlattice structure and the feature of providing a GaSb buffer layer; and document 6 discloses a pn structure, a transverse diode, a superlattice structure and the like.

Such being the case, claims 2 to 12 cannot be considered to involve an inventive step in the light of documents 1 and 3 to 6.

(3) Claims 13 and 23 can be considered to set forth inventions wherein the band gaps of the sixth through eighth compound semiconductor layers are delimited in the manner that is presented therein in order to decrease the

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element resistance of the sensor by increasing the electron mobility of the sixth compound semiconductor layer and in order to suppress the diffusion current in the sensor by means of the eighth compound semiconductor layer. On the other hand, documents 1 to 7 do not disclose the inventions in question.

Such being the case, claims 13 to 28 can be considered to involve an inventive step in relation to the abovementioned documents.